

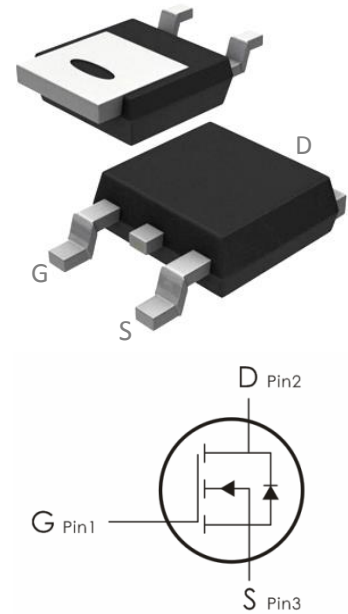
## Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge.

It can be used in a wide variety of applications.

## Features:

- 1)  $V_{DS}=40V, I_D=60A, R_{DS(ON)} < 12m\ \Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra  $R_{DS(ON)}$ .
- 5) Excellent package for good heat dissipation.



## Absolute Maximum Ratings: ( $T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current- $T_C=25^\circ C$	60	A
	Continuous Drain Current- $T_C=100^\circ C$	42	
	Pulsed Drain Current	200	
$E_{AS}$	Single Pulse Avalanche Energy <sup>5</sup>	400	mJ
$P_D$	Power Dissipation	65	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ C$

## Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case <sup>2</sup>	2.3	$^\circ C/W$

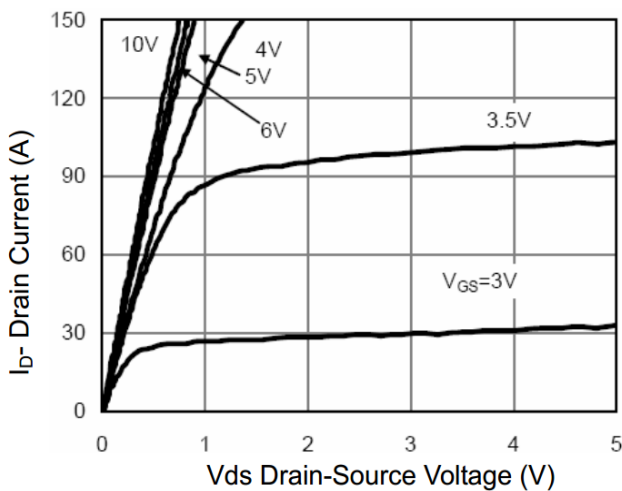
**Electrical Characteristics:** ( $T_c=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu A$	40	45	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=40V$	---	---	1	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	$\pm 100$	nA
<b>On Characteristics<sup>3</sup></b>						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu A$	1.2	1.6	2.5	V
$R_{DS(ON)}$	Drain-Source On Resistance	$V_{GS}=10V, I_D=20A$	---	7.3	12	m $\Omega$
$G_{FS}$	Forward Transconductance	$V_{DS}=10V, I_D=20A$	15	---	---	S
<b>Dynamic Characteristics<sup>4</sup></b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	---	1800	---	pF
$C_{oss}$	Output Capacitance		---	280	---	
$C_{rss}$	Reverse Transfer Capacitance		---	190	---	
<b>Switching Characteristics<sup>4</sup></b>						
$t_d(on)$	Turn-On Delay Time	$V_{DD}=20V, I_D=2A, R_L=1\Omega$ $V_{GS}=10V, R_G=3\Omega$	---	6.4	---	ns
$t_r$	Rise Time		---	17.2	---	ns
$t_d(off)$	Turn-Off Delay Time		---	29.6	---	ns
$t_f$	Fall Time		---	16.8	---	ns
$Q_g$	Total Gate Charge	$V_{GS}=10V, V_{DS}=20V,$ $I_D=20A$	---	29	---	nC
$Q_{gs}$	Gate-Source Charge		---	4.5	---	nC
$Q_{gd}$	Gate-Drain "Miller" Charge		---	6.4	---	nC
<b>Drain-Source Diode Characteristics</b>						
$V_{SD}$	Source-Drain Diode Forward Voltage <sup>3</sup>	$V_{GS}=0V, I_S=10A$	---	---	1.2	V

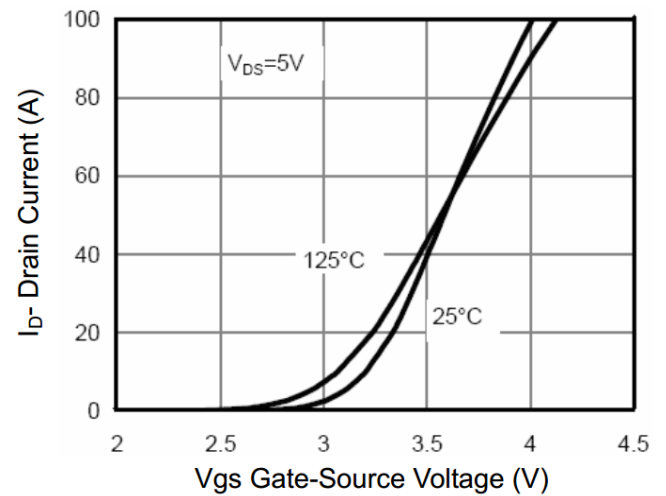
## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_j=25^\circ C, V_{DD}=20V, V_G=10V, L=1mH, R_g=25\Omega$ .

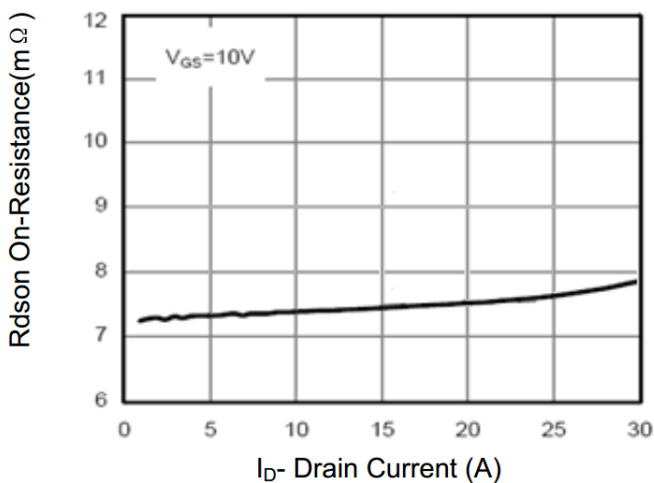
## Typical Characteristics: ( $T_c=25^\circ C$ unless otherwise noted)



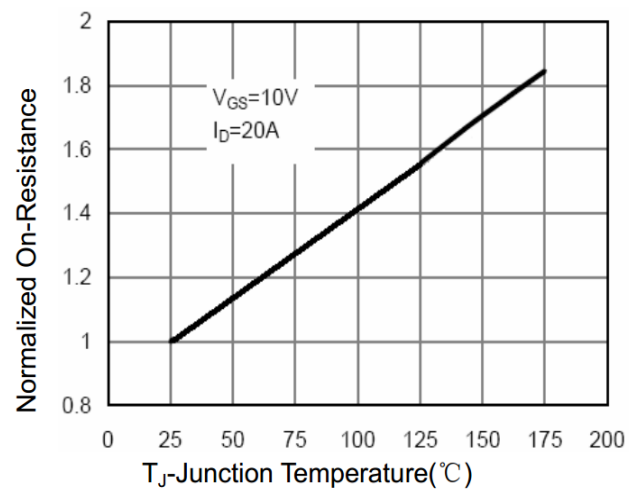
**Figure 1 Output Characteristics**



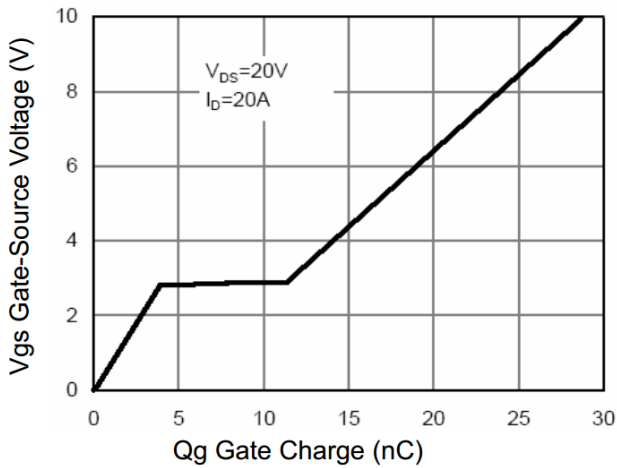
**Figure 2 Transfer Characteristics**



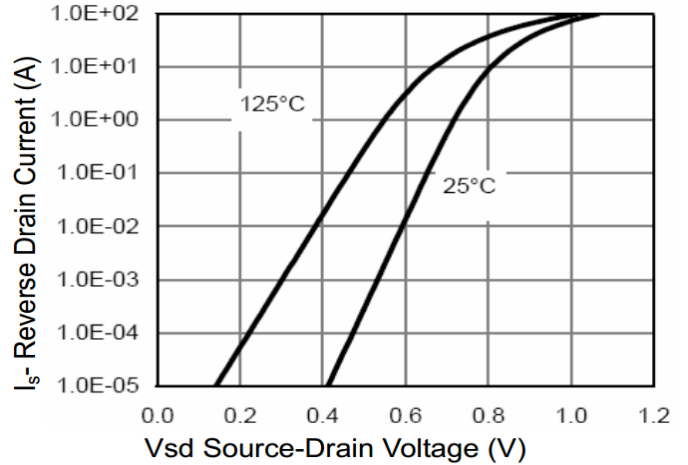
**Figure 3 Rdson- Drain Current**



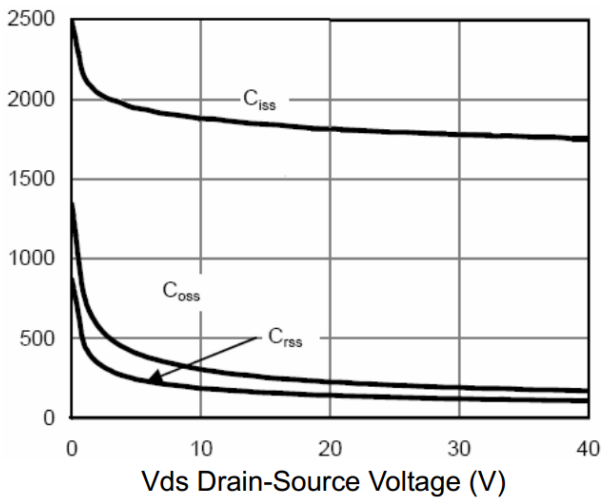
**Figure 4 Rdson-Junction Temperature**



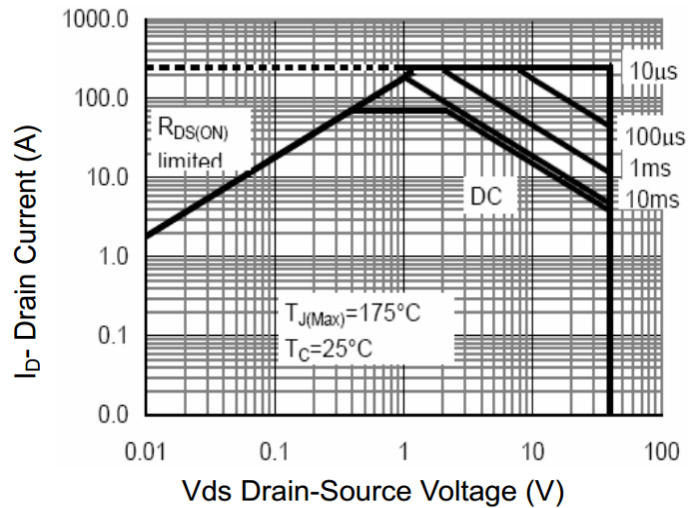
**Figure 5 Gate Charge**



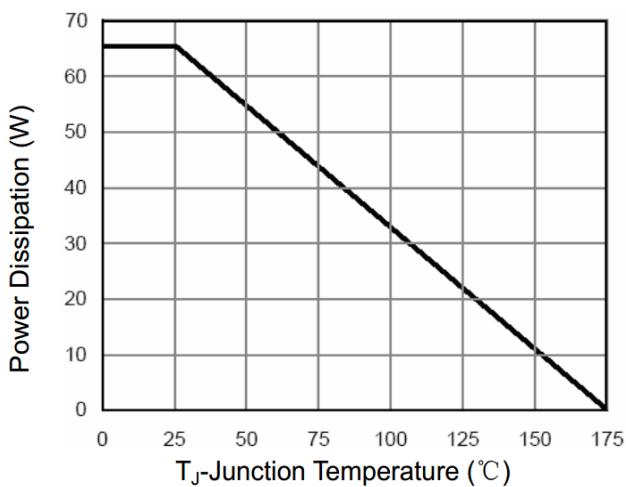
**Figure 6 Source- Drain Diode Forward**



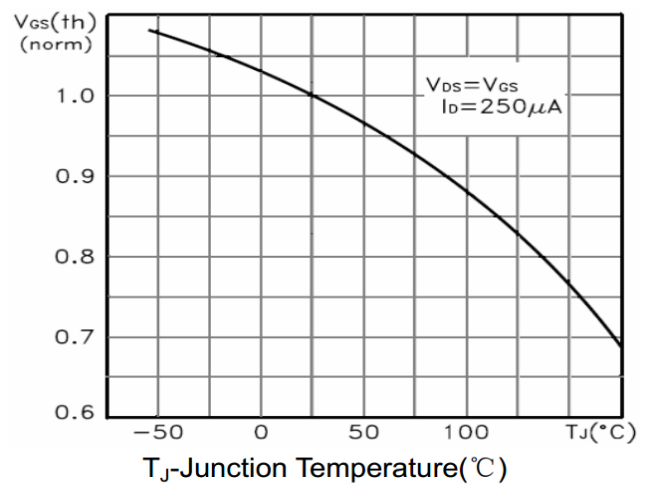
**Figure 7 Capacitance vs Vds**



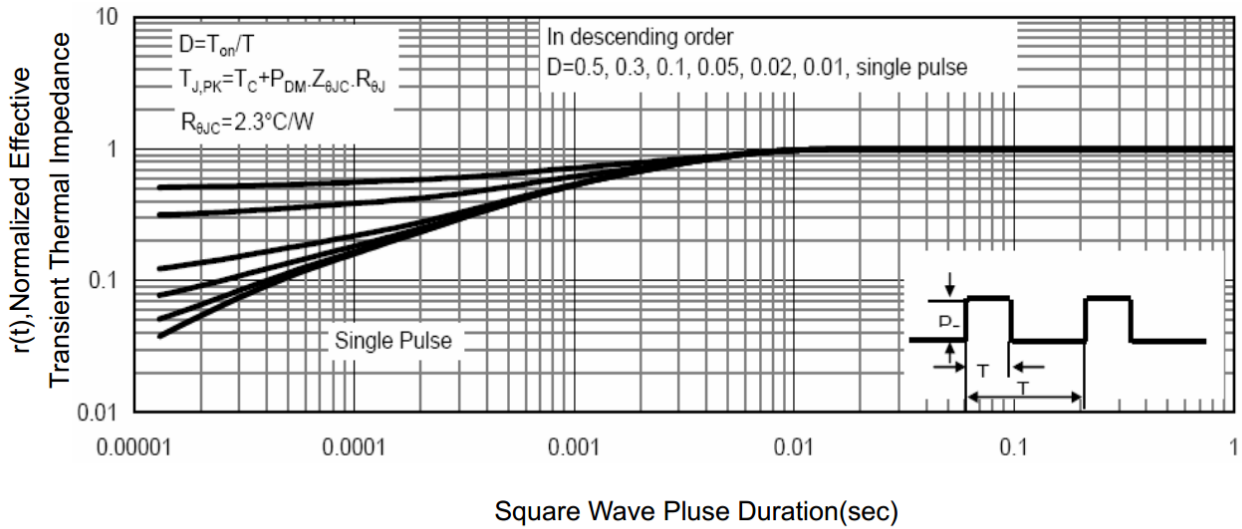
**Figure 8 Safe Operation Area**



**Figure 9 Power De-rating**



**Figure 10 V<sub>GS(th)</sub> vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**



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